NPN Silicon RF Power Transistor

... designed for 12.5 volt UHF large-signal, common-base amplifier applications in industrial and commercial FM equipment operating in the range of 806-960 MHz.

- Specified 12.5 Volt, 870 MHz Characteristics
 Output Power = 20 Watts
 Power Gain = 6.0 dB Min
 Efficiency = 50% Min
- Series Equivalent Large—Signal Characterization
- Internally Matched Input for Broadband Operation
- 100% Tested for Load Mismatch Stress at All Phase Angles with 20:1 VSWR @ 15.5 Volt Supply and 50% RF Overdrive
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- · Silicon Nitride Passivated

MRF842

20 W, 870 MHz RF POWER TRANSISTOR NPN SILICON



CASE 319-07, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	16	Vdc
Collector–Base Voltage	Vсво	36	Vdc
Emitter–Base Voltage	V _{EBO}	4.0	Vdc
Collector Current — Continuous	IC	7.6	Adc
Total Device Dissipation @ T _C = 25°C (1) Derate above 25°C	PD	80 0.64	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

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Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	1.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	27///2				
Collector–Emitter Breakdown Voltage (IC = 50 mAdc, IB = 0)	V(BR)CEO	16	_	_	Vdc
Collector–Emitter Breakdown Voltage (IC = 50 mAdc, VBE = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (IE = 10 mAdc, IC = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 15 Vdc, I _E = 0)	ICBO	_	_	5.0	mAdc

NOTES: (continued)

This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.

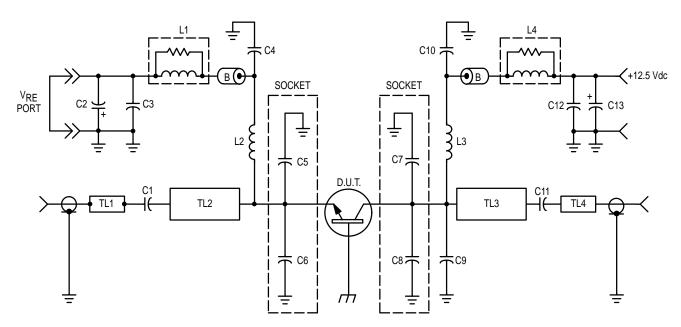
Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.



ELECTRICAL CHARACTERISTICS — **continued** (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS	•	•	•	•	
DC Current Gain (I _C = 2.0 Adc, V _{CE} = 5.0 Vdc)	hFE	10	_	_	_
DYNAMIC CHARACTERISTICS	•				
Output Capacitance (V _{CB} = 12.5 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	45	65	pF
FUNCTIONAL TESTS	•				
Common–Base Amplifier Power Gain (Pout = 20 W, V _{CC} = 12.5 Vdc, f = 870 MHz)	G _{PB}	6.0	7.0	_	dB
Collector Efficiency (P _{Out} = 20 W, V _{CC} = 12.5 Vdc, f = 870 MHz)	η	50	55	_	%
Load Mismatch Stress (V _{CC} = 15.5 Vdc, P _{in} (3) = 6.0 W, f = 870 MHz, VSWR = 20:1, all phase angles)	_	No Degradation in Output Power			

NOTE:



B — Ferrite Bead, Ferroxcube 56-590-65-3B

C1, C11 — 51 pF, 100 Mil Chip Capacitor

C2, C13 — 15 μ F, 20 WV Tantalum

C3, C12 — 1000 pF Unelco J101

C4, C10 — 91 pF Mini–Underwood

C5 — 15 pF Mini–Underwood C6 — 12 pF Mini–Underwood

C7, C8 — 21 pF Mini-Underwood

C9 — 11 pF Mini-Underwood

L1, L4 — 11 Turns #20 AWG Over 10 ohm 1/2 W Carbon

L2, L3 — 4 Turns #20 AWG, 200 Mil ID

TL1, TL4 — Micro Strip, $Z_0 = 50 \Omega$

TL2 — Micro Strip, Z_0 = 38 Ω , $\lambda/4$ @ 838 MHz TL3 — Micro Strip, Z_0 = 24 Ω , $\lambda/4$ @ 838 MHz

Board — 0.032" Glass Teflon

2 oz. Cu CLAD, ε_r = 2.55

Figure 1. 870 MHz Test Circuit Schematic

^{3.} P_{in} = 150% of the typical input power requirement for 20 W output power @ 12.5 Vdc.

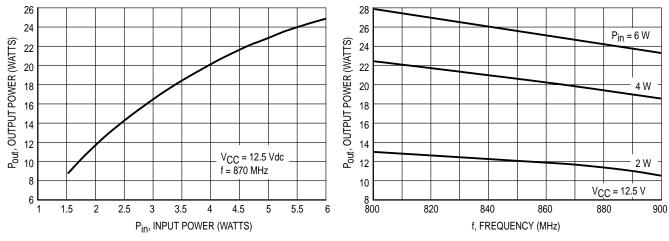


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Frequency

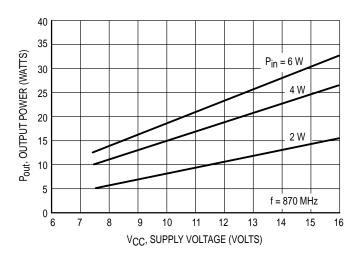
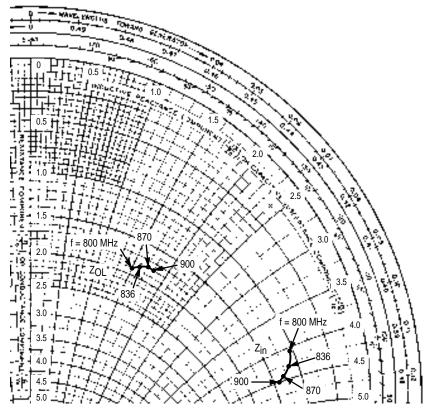


Figure 4. Output Power versus Supply Voltage



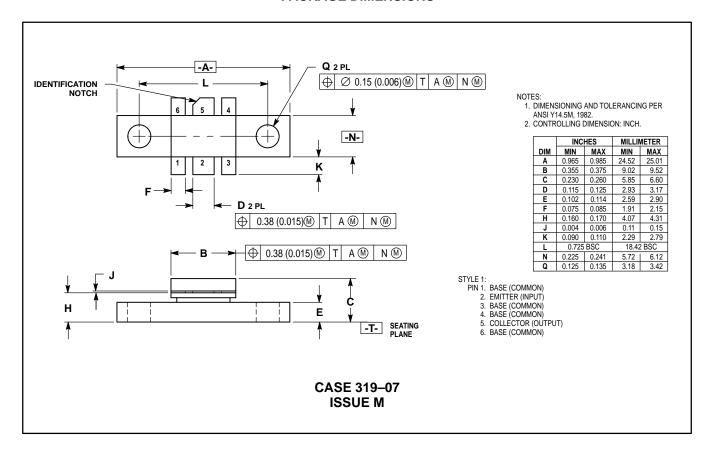
 $P_{out} = 20 \text{ W}, V_{CC} = 12.5 \text{ Vdc}$

f	Z _{in}	Z _{OL} *
MHz	Ohms	Ohms
800	1.1 + j4.1	1.9 + j1.5
836	1.2 + j4.3	1.85 + j1.6
870	1.4 + j4.4	1.8 + j1.7
900	1.6 + j4.5	1.8 + j1.8

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 5. Series Equivalent Input/Output Impedance

PACKAGE DIMENSIONS



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